



2SC6082

Bipolar Transistor 50V, 15A, Low $V_{CE(sat)}$ NPN TO-220F-3SG

ON Semiconductor®

<http://onsemi.com>

Applications

- High-speed switching applications (switching regulator, driver circuit)

Features

- Adoption of MBIT process
- Large current capacitance
- Low collector-to-emitter saturation voltage
- High-speed switching

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

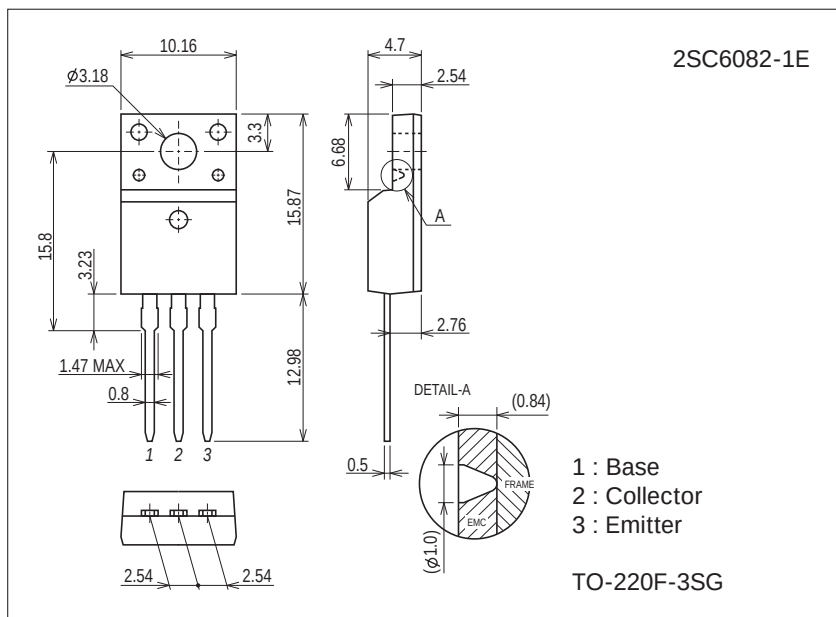
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		60	V
Collector-to-Emitter Voltage	V_{CES}		60	V
	V_{CEO}		50	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		15	A
Collector Current (Pulse)	I_{CP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	20	A
Base Current	I_B		3	A
Collector Dissipation	P_C		2	W
		$T_c=25^\circ\text{C}$	23	W
Junction Temperature	T_j		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

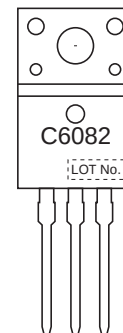
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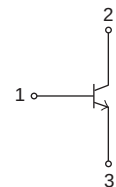
Product & Package Information

- Package : TO-220F-3SG
- JEITA, JEDEC : SC-67
- Minimum Packing Quantity : 50 pcs./magazine

Marking



Electrical Connection

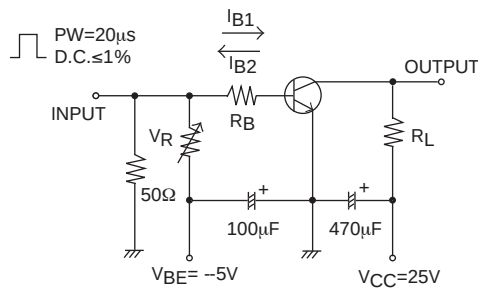


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Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	V _{CB} =40V, I _E =0A			10	μA
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0A			10	μA
DC Current Gain	h _{FE1}	V _{CE} =2V, I _C =330mA	200		560	
	h _{FE2}	V _{CE} =2V, I _C =10A	50			
Gain-Bandwidth Product	f _T	V _{CE} =10V, I _C =2A		195		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		85		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =7.5A, I _B =375mA		200	400	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =7.5A, I _B =375mA			1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _C =100μA, I _E =0A	60			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CES}	I _C =100μA, R _{BE} =0Ω	60			V
	V _{(BR)CEO}	I _C =1mA, R _{BE} =∞	50			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =100μA, I _C =0A	6			V
Turn-On Time	t _{on}	See specified Test Circuit		52		ns
Storage Time	t _{stg}			560		ns
Fall Time	t _f			37		ns

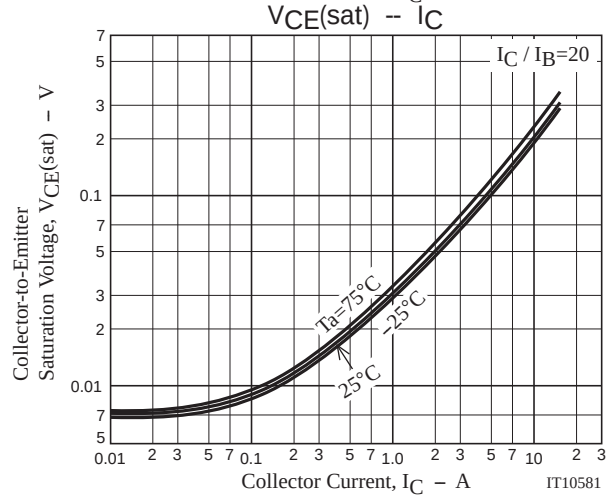
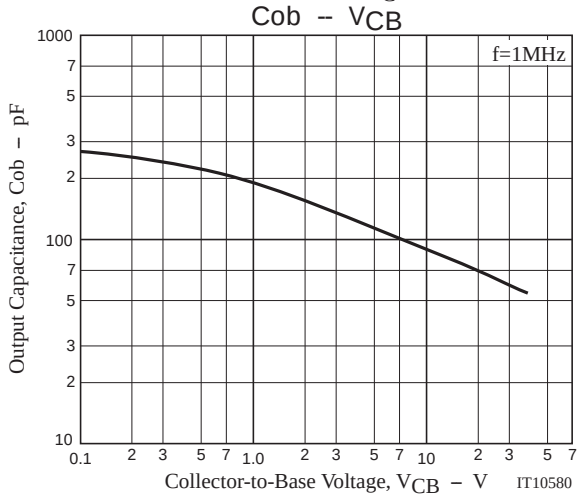
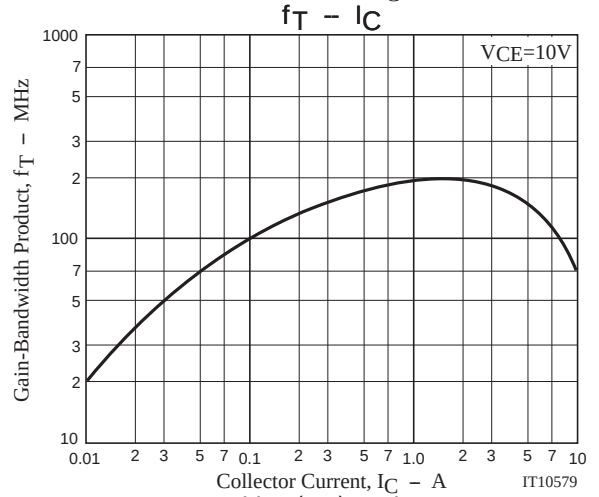
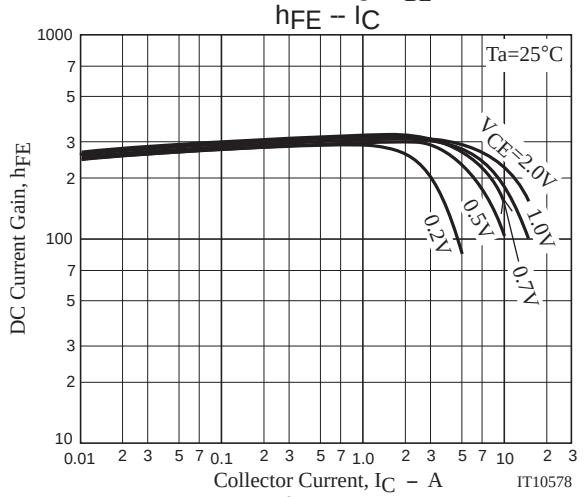
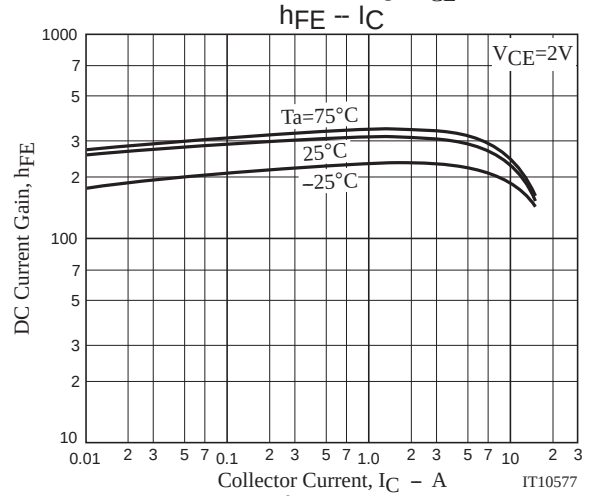
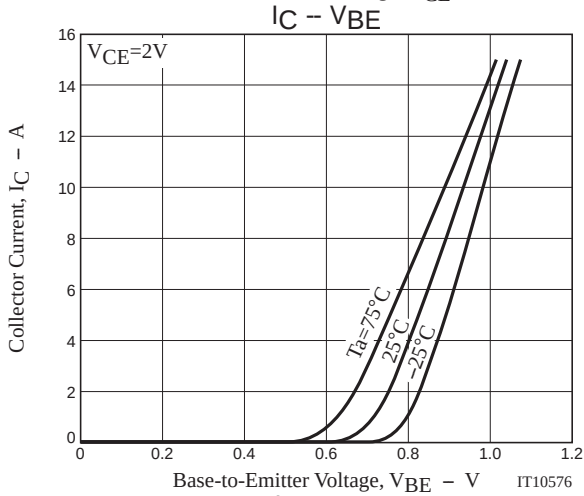
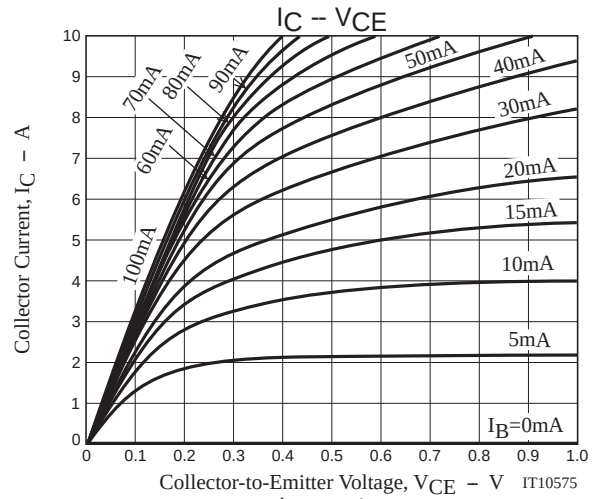
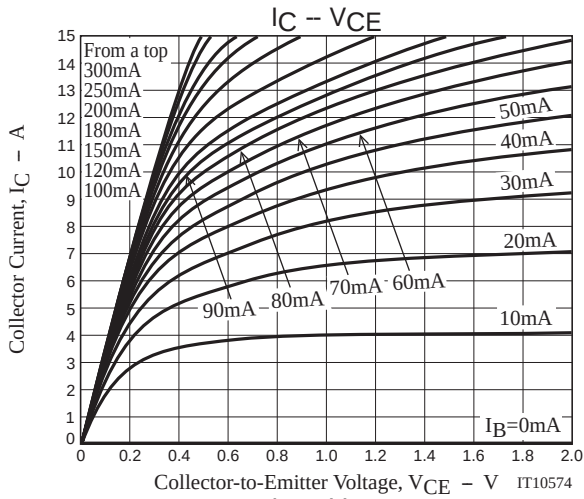
Switching Time Test Circuit

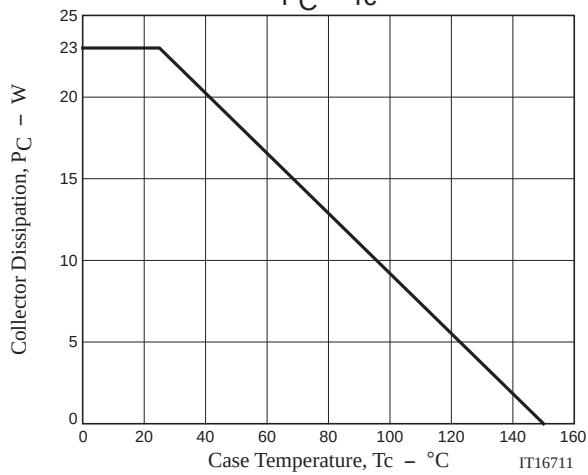
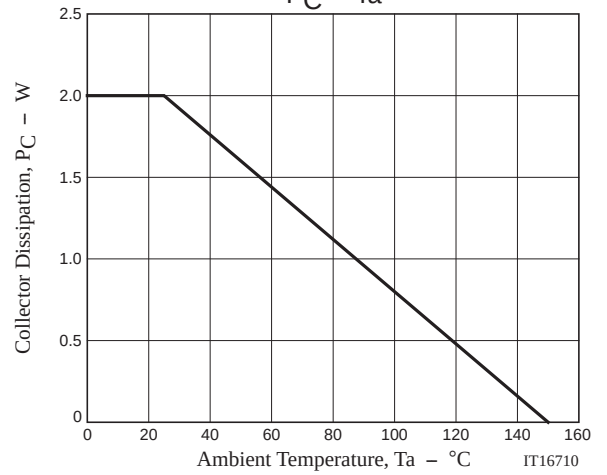
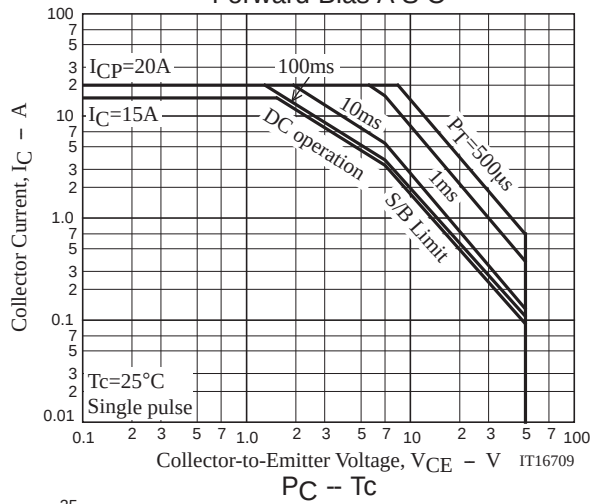
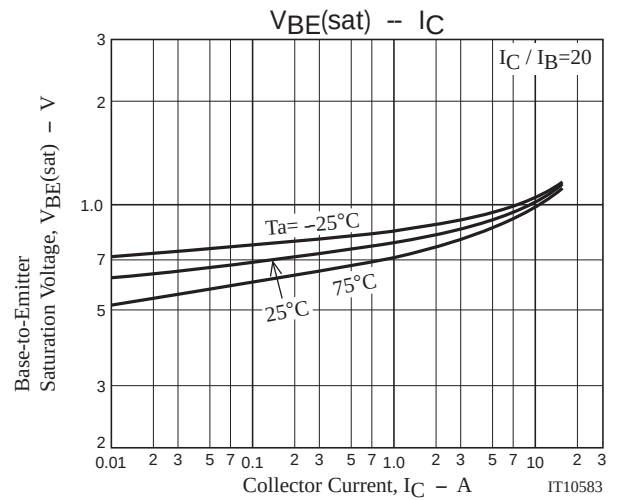
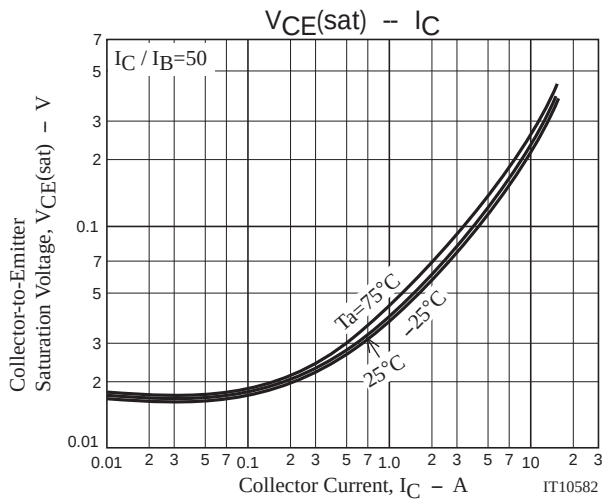


$I_C = 20I_{B1} = -20I_{B2} = 5A$

Ordering Information

Device	Package	Shipping	memo
2SC6082-1E	TO-220F-3SG	50pcs./magazine	Pb Free





Magazine Specification

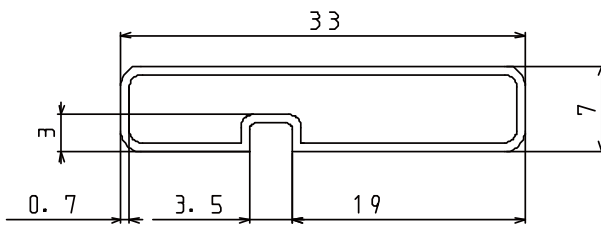
2SC6082-1E

1. Packing Format

Package Name	Magazine Name	Maximum Number of devices contained (pcs)			Packing format	
		Magazine	Inner box	Outer box	Inner BOX	Outer BOX
TO-220F-3SG	TO-220F	50	1,000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178

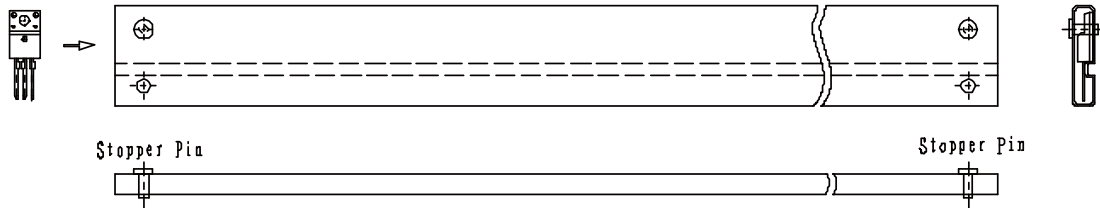
2. Magazine dimensions

(unit:mm)

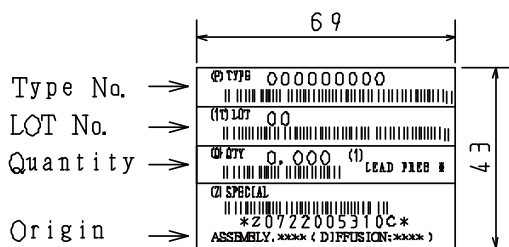


Tolerance=±0.3mm
 Thickness=0.7±0.2mm
 Length =532.5±2mm
 Material =PVC (Antistatic treatment)

3. Storage method to magazine

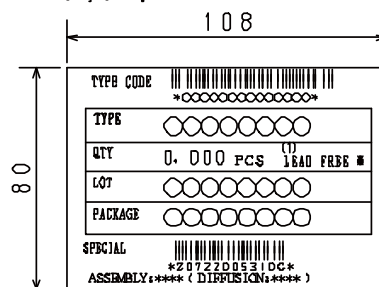


4. Inner box label (unit:mm)



5. Outer box label (unit:mm)

It is a label at the time of factory shipments.
 The form of a label may change in physical
 distribution process.



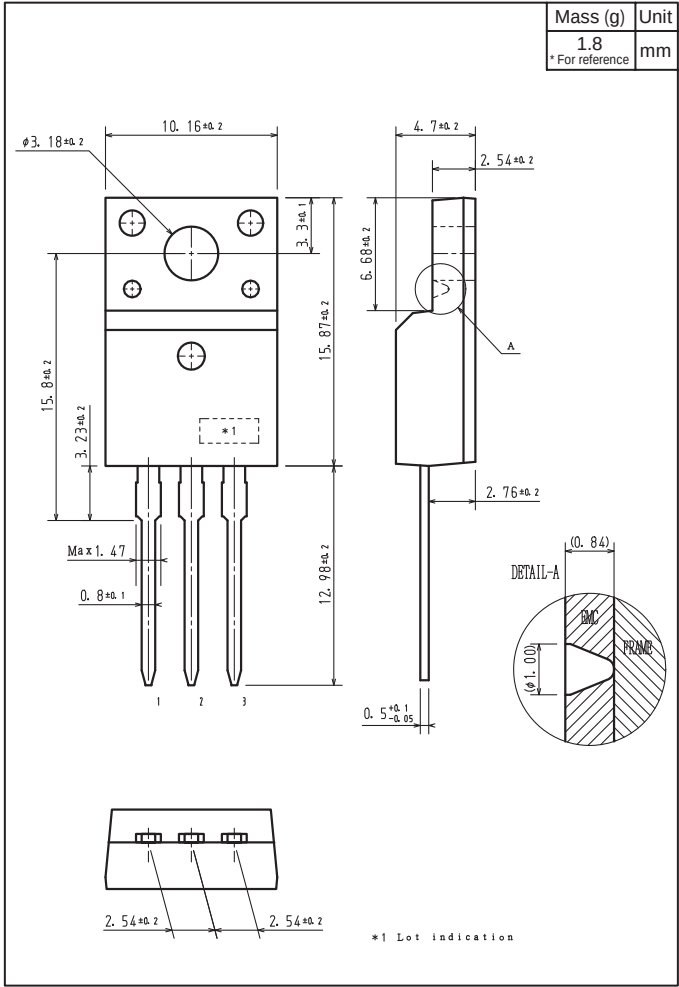
NOTE (1)

The LEAD FREE # description shows that the
 surface treatment of the terminal is lead free.

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A

Outline Drawing

2SC6082-1E



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